

TAKING

THE

MYSTERY

OUT OF

THIN-FILM MEASUREMENT

FILMETRICS
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THIN-FILM MEASUREMENT

Introduction

Thin film

Thin films are very thin layers of material that are deposited on the surface of another material. They provide extremely important capabilities to many industries. For example, thin films are widely used to provide passivation (insulating layers between conductors), and diffusion barriers for faster processing speed in electronic circuits. Hardness coatings for scratch resistance and antireflection coatings are also thin films.

The thickness of films used in thin-film applications range from less than 10 Å (a few atoms) to 100 μm (the width of a human hair.) They can be formed by many different processes, including spin coating, vacuum evaporation, sputtering, vapor deposition, planarization, and dip coating.

To perform the functions for which they were designed, thin films must have the proper thickness, composition, roughness, and other characteristics important to the particular application. These characteristics must often be measured, both during and after fabrication.

The two main classes of thin-film measurement are optical and stylus-based techniques. Stylus measurements measure thickness and roughness by monitoring the deflections of a fine-tipped stylus as it is dragged along the surface of the film. Stylus instruments are limited in speed and accuracy, and they require a “step” in the film to measure thickness. They are often the preferred method, however, when measuring opaque films, such as metals.

Optical techniques determine thin-film characteristics by measuring how the light interacts with the films. Optical techniques can measure the thickness, roughness, and optical constants of a film. Optical constants describe how light propagates through and reflects from a material. Once known, optical constants can be related to other material parameters, such as composition and band gap.

Optical techniques are usually the preferred method for measuring thin films because they are accurate, nondestructive, and require little or no sample preparation. The two most common optical measurement types are spectral reflectance and ellipsometry. Spectral reflectance measures the amount of light reflected from a thin film over a range of wavelengths, with the incident light perpendicular to the sample surface. Ellipsometry is similar, except that it measures reflectance at non-normal incidence and at two different polarizations. In general, spectral reflectance is much simpler and less expensive than ellipsometry, but it is restricted to measuring less complex structures.

n and *k* Definitions

Optical constants (*n* and *k*) describe how light propagates through a film. In simple terms, the electromagnetic field that describes light traveling through a material at a fixed time is given by:

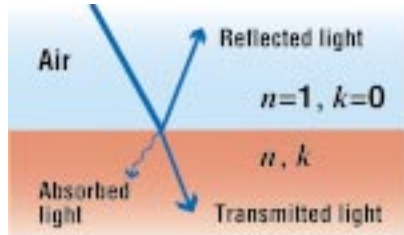
$$E = A \cdot \cos \left(n \frac{2\pi}{\lambda} x \right) \cdot \exp \left(-k \frac{2\pi}{\lambda} x \right)$$

where *x* is distance, λ is the wavelength of light, and *n* and *k* are the film's refractive index and extinction coefficient, respectively. The refractive index is defined as the ratio of the speed of light in a vacuum to the speed of light in the material ($n = \frac{c}{v}$). The extinction coefficient is a measure of how much light is absorbed in the material.

Spectral Reflectance Basics

Single Interface

Reflection occurs whenever light crosses the interface between different materials. The fraction of light that is reflected by an interface is determined by the discontinuity in n and k . The equation for light reflected off of a material in air is:

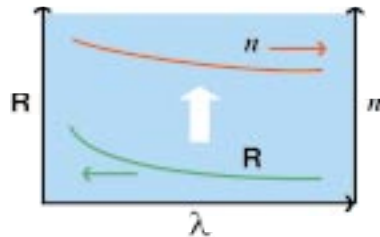


The equation for light reflected off of a material in air is:

$$R = \frac{(n-1)^2 + k^2}{(n+1)^2 + k^2}$$

To see how spectral

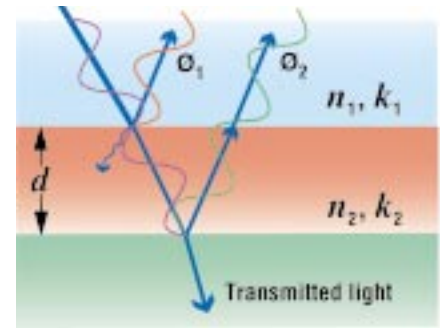
reflectance can be used to measure optical constants, consider the simple case of light reflected by a single nonabsorbing material ($k=0$). Then: $R = \left| \frac{n-1}{n+1} \right|^2$. Clearly, n of the material can be determined from a measurement of R . In real materials, n varies with wavelength (that is to say, real materials exhibit dispersion), but since the reflectance is known at many wavelengths, n at each of these wavelengths is also known, as shown here.



Multiple Interfaces

Consider now a thin film on top of another material. In this case both the top and bottom of the film reflect light. The total amount of reflected light is the sum of these two individual reflections. Because of the wavelike nature of light, the reflections from the two interfaces may add together either constructively (intensities add)

or destructively (intensities subtract), depending upon their phase relationship. Their phase relationship is determined by the difference in



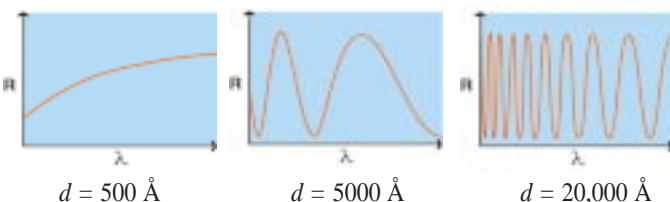
optical path lengths of the two reflections, which in turn is determined by thickness of the film, its optical constants, and the wavelength of the light. Reflections are in-phase and therefore add constructively when the light path is equal to one integral multiple of the wavelength of light. For light perpendicularly incident on a transparent film, this occurs when $2nd = i\lambda$, where d is the thickness of the film and i is an integer (the factor of two is due to the fact that the light passes through the film twice.) Conversely, reflections are out of phase and add destructively when the light path is one half of a wavelength different from the in-phase condition, or when $2nd = (i + 1/2)\lambda$. The qualitative aspects of these reflections may be combined

into a single equation:

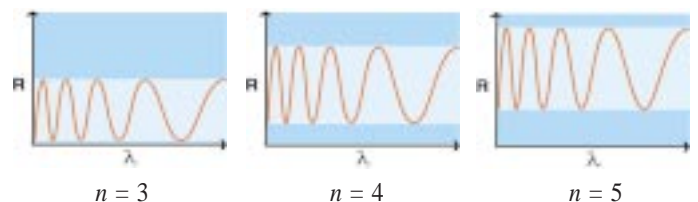
$$R \approx A + B \cos \left(\frac{2\pi}{\lambda} nd \right)$$

From this, we can see that the reflectance of a thin film will vary periodically with $1/\text{wavelength}$, which is illustrated below. Also, thicker films will exhibit a greater number of oscillations over a given wavelength range, while thinner films will exhibit fewer oscillations, and oftentimes only part of an oscillation, over the same range.

Determination of thickness (d)



Determination of refractive index (n)

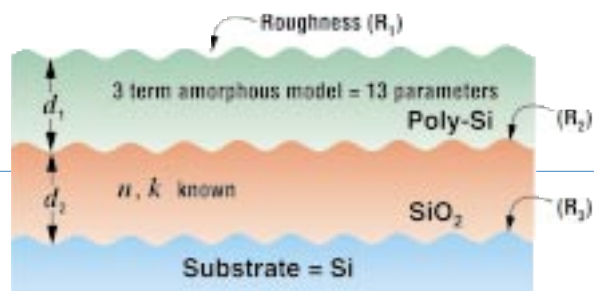


Determining Film Properties from Spectral Reflectance

The amplitude and periodicity of the reflectance of a thin film is determined by the film's thickness, optical constants, and other properties such as interface roughness. In cases where there is more than one interface, it is not possible to solve for film properties in closed form, nor is it possible to solve for n and k at each wavelength individually. In practice, mathematical models are used that describe n and k over a range of wavelengths using only a few adjustable parameters. A film's properties are determined by calculating reflectance spectra based on trial values of thickness and the n and k model parameters, and then adjusting these values until the calculated reflectance matches the measured reflectance.

Models for n and k

There are many models for describing n and k as a function of wavelength. When choosing a model for a particular film, it is important that the model be able to accurately describe n and k over the wavelength range of interest using as few parameters as possible. In general, the optical constants of different classes of materials (e.g., dielectrics, semiconductors, metals, and amorphous materials) vary quite differently with wavelength, and require different models to describe them (see below.) Models for dielectrics ($k=0$) generally have three parameters, while nondielectrics generally have five or more parameters. Therefore, as an example, to model the two-layer structure shown below, a total of 18 adjustable parameters must be considered in the solution.



Mathematical Models for n & k

Cauchy:
$$n(\lambda) = A + \frac{B}{\lambda^2} + \frac{C}{\lambda^4}$$

$$k(\lambda) = 0$$

Fitting parameters: A, B, C (total of 3)

Amorphous Semiconductor:
$$\epsilon_2(E) = 2nk = \sum_{i=1}^{j=1,2 \text{ or } 3} \frac{A_i C_i E_{0i} (E - E_{gi})^2}{(E^2 - E_{0i}^2)^2 + C_i^2 E^2} \cdot \frac{1}{E} \quad \text{If } E > E_g, \text{ or } = 0 \text{ if } E < E_g$$

$$\epsilon_1(E) = n^2 - k^2 = \epsilon_1(\infty) + \frac{2P}{\pi} \int_0^\infty \frac{s \epsilon_2(s)}{s^2 - E^2} ds \quad \text{(Kramers-Kronig relationship)}$$

Fitting parameters: $\epsilon_1(\infty)$, A_1 , C_1 , E_{g1} , E_{01} , ... (total of 5, 9 or 13)

Crystalline Semiconductor:
$$\epsilon_2(E) = 2nk = \sum_{i=1}^{j=1,2 \text{ or } 3} \frac{A_i}{B_i + (E - E_{0i})^2}$$

$$\epsilon_1(E) = n^2 - k^2 = \epsilon_1(\infty) + \frac{2P}{\pi} \int_0^\infty \frac{s \epsilon_2(s)}{s^2 - E^2} ds \quad \text{(Kramers-Kronig relationship)}$$

Fitting parameters: $\epsilon_1(\infty)$, A_1 , B_1 , E_{01} , ... (total of 4, 7 or 10)

Number of Variables,

Limitations of Spectroscopic Reflectance

Spectral reflectance can measure the thickness, roughness, and optical constants of a broad range of thin films. However, if there is less than one reflectance oscillation (ie. the film is very thin), there is less information available to determine the adjustable model parameters. Therefore, the number of film properties that may be determined decreases for very thin films. If one attempts to solve for too many parameters, a unique solution cannot be found; more than one possible combination of parameter values may result in a calculated reflectance that matches the measured reflectance.

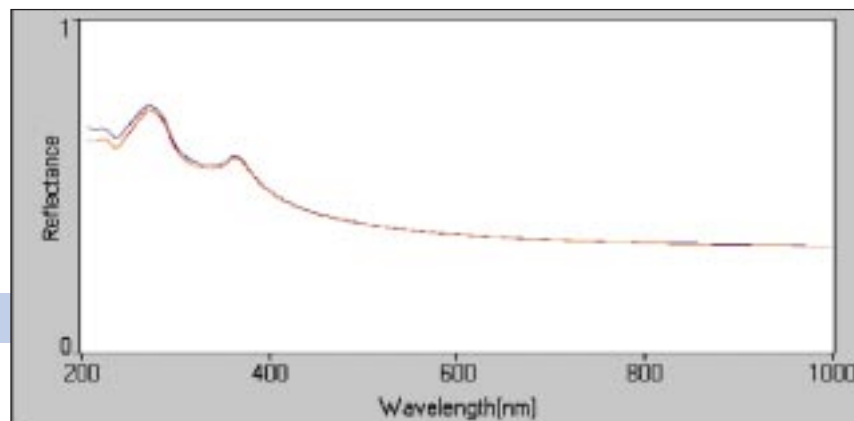
An example of the reflectance from a very thin film, 50 Å of SiO₂ on silicon is shown below, where it is compared to the reflectance from a bare silicon substrate. In this case, measuring the thickness, roughness, and n of the SiO₂ requires five parameters to be determined. Clearly, the change in the spectra caused by adding 50 Å of SiO₂ does not require five parameters to describe, and a unique solution cannot be found unless some additional assumptions are made.

Depending upon the film and the wavelength range of the measurement, the minimum single-film thickness that can be measured using spectral reflectance is in the 10 Å to 300 Å range. If one is trying to measure optical constants as well, the minimum thickness increases to between 500 Å and 2000 Å, unless minimal parameterization models can be used. When solving for the optical properties of more than one film, the minimum thicknesses are increased even further.

Spectroscopic Reflectance versus Ellipsometry

Given the restrictions listed above, spectral reflectance can be used to measure a large percentage of technologically important films. However, when films are too thin, too numerous, or too complicated to be measured with spectral reflectance, oftentimes they can be measured with the generally more powerful technique of spectroscopic ellipsometry. By measuring reflectance at non-normal incidence (typically around 75° from normal) ellipsometry is more sensitive to very thin layers, and the two different polarization measurements provide twice as much information for analysis. To carry the idea even further, variable-angle ellipsometry can be used to take reflectance measurements at many different incidence angles, thereby increasing the amount of information available for analysis.

The following pages of this brochure describe spectral reflectance systems available from Filmetrics. If you are uncertain whether spectral reflectance or ellipsometry is appropriate for your film measurements, please call us to discuss your application. If spectral reflectance cannot satisfy your needs, we will be happy to refer you to a reputable source for ellipsometry.



Thin-Film Measurements on your bench top

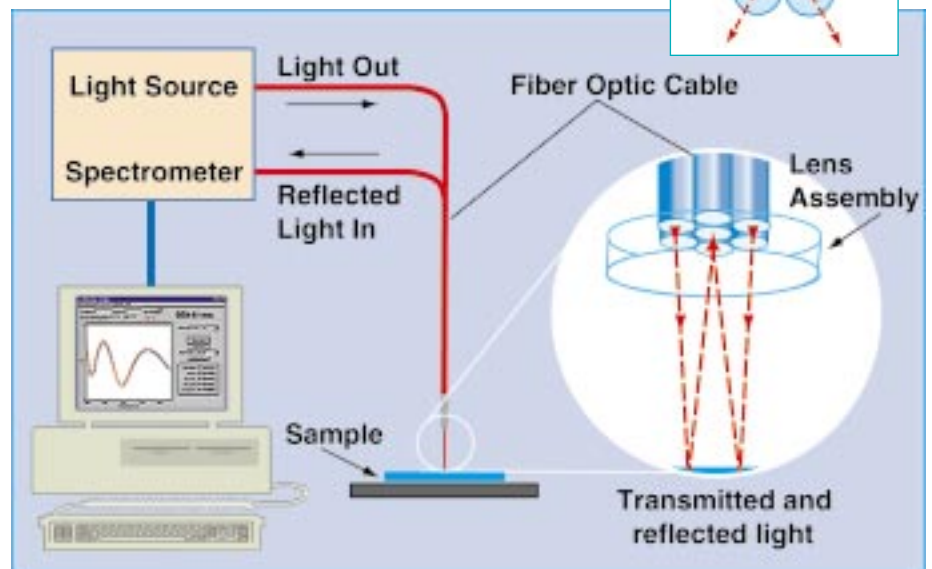
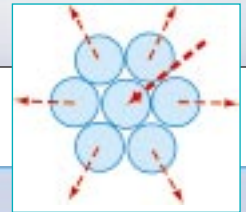
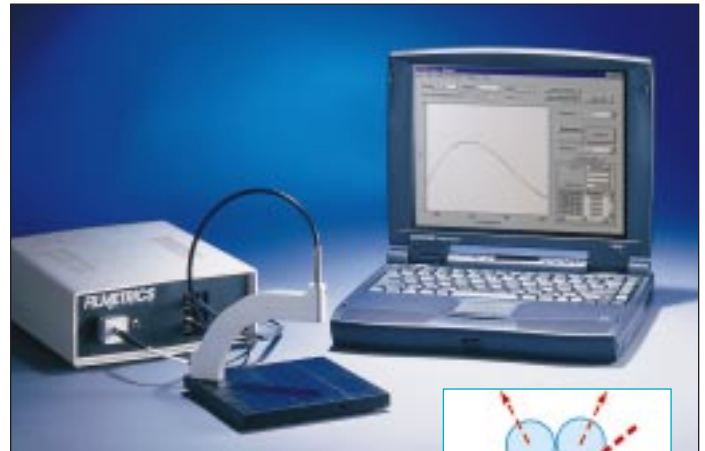
Thickness, refractive index, and extinction coefficients are measured quickly and easily with Filmetrics' advanced spectrometry systems. Simply plug the Filmetrics system into your computer's parallel port and start making measurements. The entire system sets up in minutes and measurements can be made by anyone with basic computer skills. This simple hardware and intuitive software provides thin-film knowledge to a whole new group of users.

From near infrared to ultraviolet

Systems are available with wavelengths from 215 nm to 1020 nm, enabling measurements of films 30 Å to 50 μm thick. The Filmetrics systems measure transparent thin films made from virtually all common materials.

Easy to use software

The familiar and user friendly interface provided by Filmetrics software is quickly mastered. Measurements are made at about one per second. Measured data, along with measurement details, are easily saved and exported with standard Windows file saving and clipboard methods. Plus, Dynamic Data Exchange allows for easy integration with other programs.



AWARD WINNING PRODUCTS

R&D 100 Award

The Filmetrics' in-situ system, Model F30, was selected as one of the 100 most technologically significant new products of 1997 by R&D Magazine.



COMPLEX MEASUREMENTS MADE SIMPLE

The system operates with standard Windows commands

One measurement – One mouse click

Choose from a list of common film types, or define your own

Both the measured and calculated reflectance spectra are displayed so that the integrity of the measurement may easily be judged. The measured n and k curves may also be plotted.

Measurement results are displayed in an easy-to-read format

A wide range of reflectance wavelengths are available, from 215 to 1020 nm

Tables of measured reflectance, n , and k data are easily accessible

The screenshot shows the FIL Measure software interface. At the top, there is a menu bar with 'File', 'Edit', 'Set Up', 'Acquire', 'Window', and 'Help'. Below the menu bar, there are input fields for 'Sample ID: Slot 14', 'Operator: Jennifer K.', and 'Cursor Wavelength(nm): 479.68'. A legend indicates that the blue line represents 'Measured Data' and the red line represents 'Calculation'. The main plot area shows 'Reflectance' on the y-axis (ranging from 0 to 1) and 'Wavelength(nm)' on the x-axis (ranging from 300 to 900). The plot displays two overlapping curves: a blue line for measured data and a red line for calculated data. To the right of the plot is a control panel with a 'Measure' button, a 'ReAnalyze' button, and a 'Structure' dropdown menu set to 'PTFE on Si'. Below these are 'Display: Layer 1 Results', a list of parameters (Thickness, n, k, Roughness, Fitting Error) with their values, and a table of measured data. The table has columns for 'Wavelength' and 'Reflectance'. Below the table are buttons for 'Select All', 'Save n,k,t Data', and 'Copy Selected Data'.

Thickness	689.2 nm
n(632.8 nm)=	1.3450
k(632.8 nm)=	0.0000
Roughness=	17.19 nm
Fitting Error =	0.009253

Wavelength	Reflectance
631.02 nm	0.3294
631.93 nm	0.3300

Photonics Spectra Circle of Excellence

The Filmetrics' F20 was chosen as one of the 25 most significant new products of 1998 by Photonics Spectra Magazine.

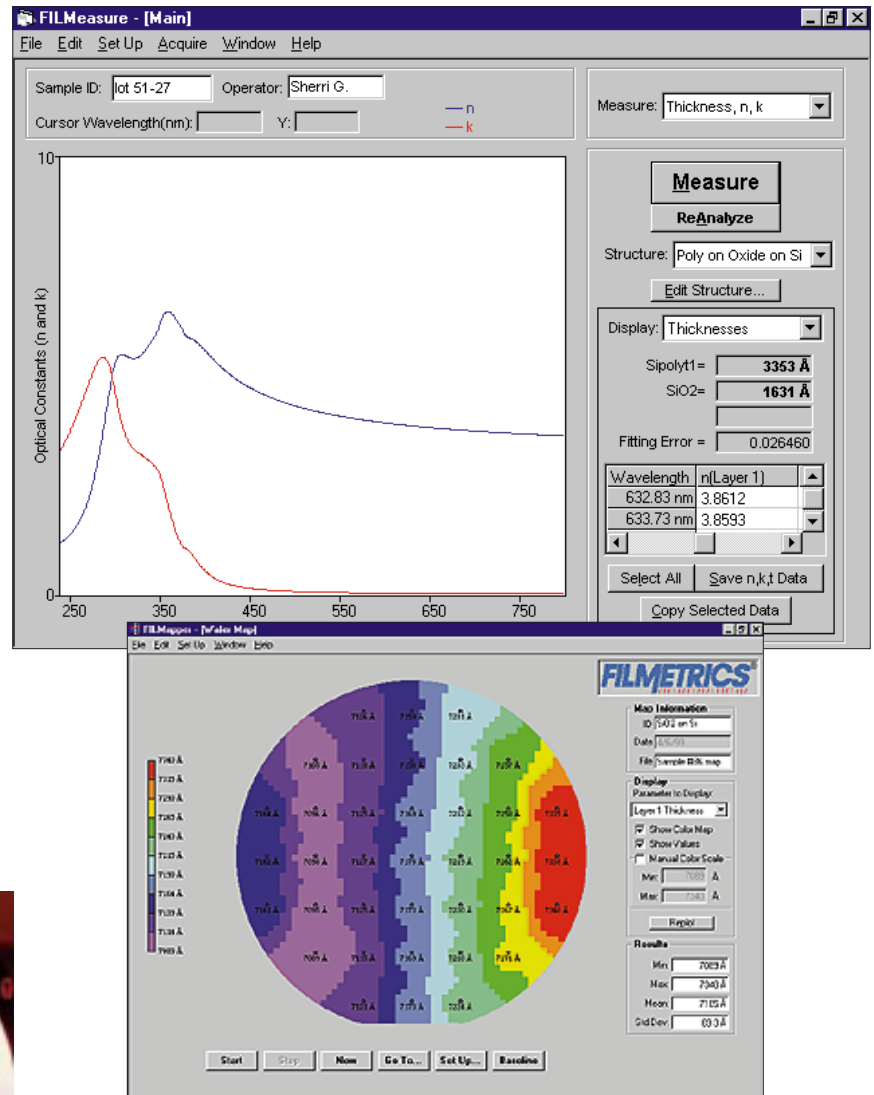


REAL WORLD APPLICATIONS

Semiconductor Process Films—

Lab / Process

Filmetrics measurement systems are routinely used to measure the thickness, roughness, and optical constants of oxides, SiN_x , photoresist, and other semiconductor process films. In addition to these single layer applications, many two- and three-layer film measurements are also possible. An example is polysilicon/ SiO_2 on silicon, which is used in SOI applications. The screen to the right shows a typical measurement result for the structure modeled on page 4.

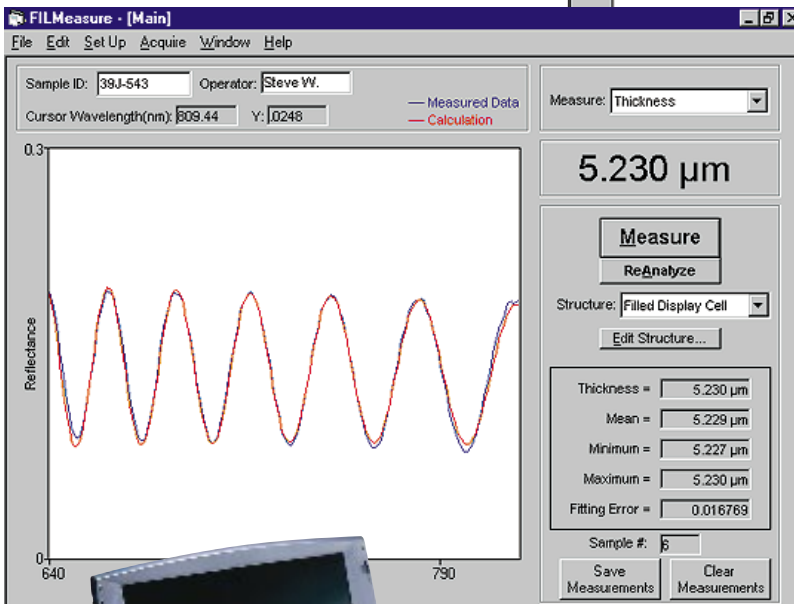
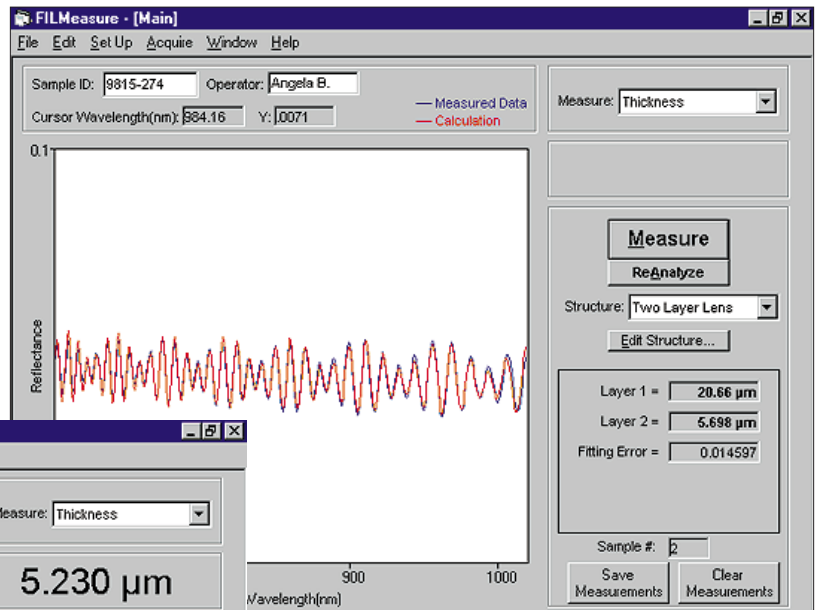


In-Situ Measurements —

The flexible optical probe assembly makes on-line and in-situ thickness measurements possible. All that is required is optical access for normal-incidence reflectance measurements. Call us for more details about interfacing with your production equipment.

Optical Coatings —

Thin films are also used for scratch resistant and antireflection coatings. Automotive plastics, eyeglass lenses, and many plastics packaging applications use thin films. For hardcoats, a primer layer is often applied first for improved film adhesion. Filmetrics systems are capable of measuring the thickness of these layers individually or simultaneously, regardless of the presence of coatings on the backside of the sample.



Flat Panel Display Applications —

Proper polyimide and resist thicknesses are critical to yield in flat panel display manufacturing. Besides measuring these materials, Filmetrics systems can also measure cell gap spacing, for both empty and filled cells.

F20

Thin-Film Measurements in Seconds

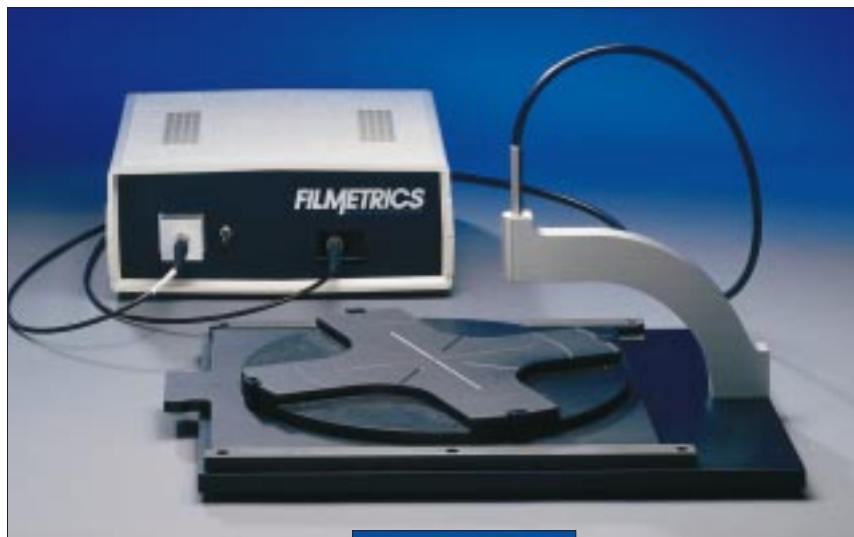
Bench top measurements of thickness, optical constants (n and k) and transmittance are made quickly and easily by the Model F20. This versatile hardware can be configured to measure transparent or translucent films that are 30 Å to 50 μm in thickness. Typical accuracy is within a few angstroms. Spot size is adjustable over a wide range.

Accessories

A wide variety of stages, chucks, and special measurement heads are available to accommodate most sample geometries.

Surprisingly Low Price

Filmetrics is pleased to offer a breakthrough price. F20 systems start at less than \$12,000. The difficult and expensive task of thin-film measurement is now simple and inexpensive.



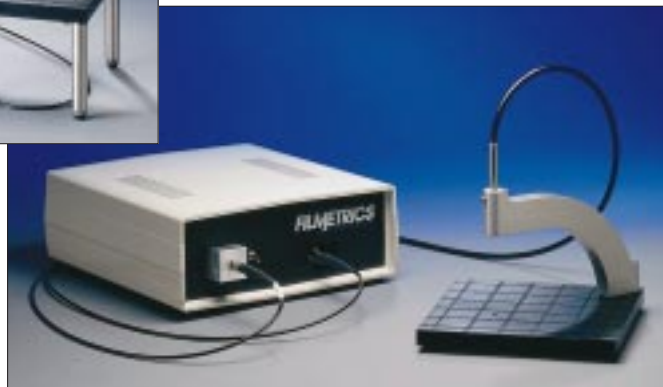
Manually maneuverable wafer chucks make sample handling easy



Accessories are available for measuring nonstandard samples



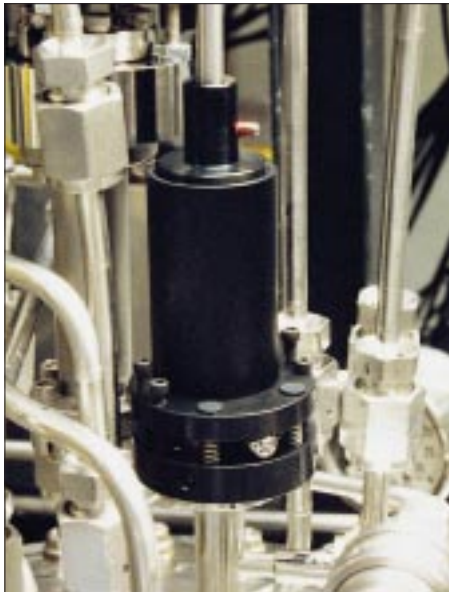
Transmittance may be measured with a simple stage modification



F30

In-Situ Measurements

For process applications, Filmetrics offers systems that need only optical access. Interfaces to a wide range of control systems are available.



F40

Turn Your Microscope into a Film Thickness Measurement Tool

The F40 is designed for thickness measurements on patterned surfaces and other applications that require a spot size as small as 10 microns.

For most common microscopes, the F40 is a simple bolt-on attachment. Standard c-mount adapter provided for CCD camera viewing of measurement location.



F50

Thickness Mapping System

This system extends the F20 thickness measurement functionality and intuitive operation to automated mapping of large area samples.

Map sample uniformity in minutes. Five points to hundreds of points as fast as one second per point. Standard chucks available for up to 12" diameter wafers. Custom chucks also available.



Models - for complete specifications, visit our [Web site](#)

Model	Thickness Measurement Range*	
	Thickness only	Thickness with <i>n</i> and <i>k</i>
F20	150 Å to 50 µm [†]	1000 Å to 5 µm
F20-UV	30 Å to 20 µm	500 Å to 5 µm
F30	1000 Å to 50 µm	1000 Å to 5 µm
F40	200 Å to 20 µm	n/a
F50	300 Å to 50 µm [†]	n/a

F20 Performance Specifications

- Spot Size
Adjustable 500 µm to 1 cm
- Sample Size
From 1 mm to 300 mm diameter and up
- Thickness Accuracy
± 1 nm at 500 nm thickness
- Precision¹
0.1 nm
- Repeatability²
0.07 nm

System Specifications

- Spectrometer Type
Fixed Czerny-Turner with 512-element photodiode array
- Light Source
Regulated Tungsten Halogen
- Computer Requirements
System running Windows™ 95/98/NT with available parallel port
5 MB hard disk space
2 MB free memory
- Power Requirements
100-240 VAC, 50-60 Hz, 0.3-0.1 A
- Warranty
1 year parts and labor

* Typical values
[†] Custom configuration available to measure thickness up to 100 µm.
¹ Standard deviation of 100 thickness readings of 500 nm SiO₂ film on silicon substrate. Value is average of standard deviations measured over twenty successive days.
² Two sigma based on daily average of 100 readings of 500 nm SiO₂ film on silicon.

Questions?

Please call us if you would like more information about measuring your thin films, or to arrange for a free trial measurement.

International customers will find a complete list of agents on our web site.

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